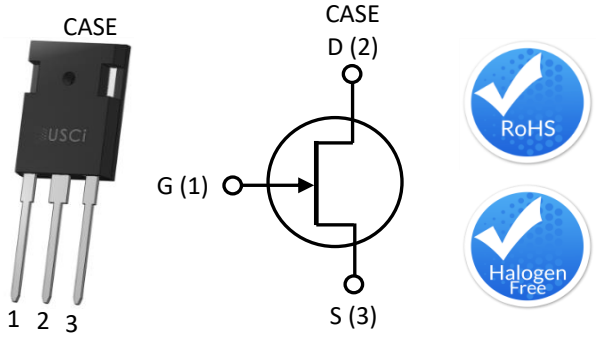
SiC JFET Division

Is Now Part of

To learn more about onsemi™, please visit our website at
www.onsemi.com

Description

United Silicon Carbide, Inc offers the high-performance G3 SiC normally-on JFET transistors. This series exhibits ultra-low on resistance ($R_{DS(ON)}$) and gate charge (Q_G) allowing for low conduction and switching loss. The device normally-on characteristics with low $R_{DS(ON)}$ at V_{GS} = 0 V is also ideal for current protection circuits without the need for active control, as well as for cascode operation.



Part Number	Package	Marking
UJ3N120035K3S	TO-247-3L	UJ3N120035K3S

Features

- Typical on-resistance $R_{DS(on),typ}$ of 35mΩ
- Voltage controlled
- Maximum operating temperature of 175°C
- Extremely fast switching not dependent on temperature
- Low gate charge
- Low intrinsic capacitance
- RoHS compliant

Typical Applications

- Over current protection circuits
- DC-AC inverters
- Switch mode power supplies
- Power factor correction modules
- Motor drives
- Induction heating

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
Drain-source voltage	V_{DS}		1200	V
Gate-source voltage	V_{GS}	DC	-20 to +3	V
		AC (1)	-20 to +20	
Continuous drain current (2)	I_D	T_C = 25°C	63	A
		T_C = 100°C	46	A
Pulsed drain current (3)	I_{DM}	T_C = 25°C	185	A
Power dissipation	P_{tot}	T_C=25°C	429	W
Maximum junction temperature	$T_{J,max}$		175	°C
Operating and storage temperature	T_J, T_{STG}		-55 to 175	°C
Max. lead temperature for soldering, 1/8" from case for 5 seconds	T_L		250	°C

(1) +20V AC rating applies for turn-on pulses <200ns applied with external R_G > 1Ω.
(2) Limited by $T_{J,max}$
(3) Pulse width t_p limited by $T_{J,max}$

Electrical Characteristics (T_J = +25°C unless otherwise specified)

Typical Performance - Static

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Drain-source breakdown voltage	BV_{DS}	V_{GS}= - 20V, I_D=1mA	1200			V
Total drain leakage current	I_D	V_{DS} = 1200V, V_{GS} = -20V, T_J = 25°C		10	60	µA
		V_{DS} = 1200V, V_{GS} = -20V, T_J = 175°C		35		
Total gate leakage current	I_G	V_{GS}=-20V, T_j=25°C		12	100	µA
		V_{GS}=-20V, T_j=175°C		50		
Drain-source on-resistance	$R_{DS(on)}$	V_{GS}=2V, I_D=20A, T_J = 25°C		31		mΩ
		V_{GS}=0V, I_D=20A, T_J = 25°C		35	45	
		V_{GS}=2V, I_D=20A, T_J = 175°C		68		
		V_{GS}=0V, I_D=20A, T_J = 175°C		76		
Gate threshold voltage	$V_{G(th)}$	V_{DS}= 5V, I_D = 70mA	-14	-11.5	-6	V
Gate resistance	R_G	f = 1MHz, open drain		2.4		Ω

Typical Performance - Dynamic

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Input capacitance	C_{iss}	V_{DS} = 100V, V_{GS} = -20V, f = 100kHz		2145		pF
Output capacitance	C_{oss}			180		
Reverse transfer capacitance	C_{rss}			172		
Effective output capacitance, energy related	$C_{oss(er)}$	V_{DS} = 0V to 800V, V_{GS} = -20V		105		pF
Total gate charge	Q_G	V_{DS}=800V, I_D = 40A, V_{GS}=-18V to 0V		235		nC
Gate-drain charge	Q_{GD}			130		
Gate-source charge	Q_{GS}			25		
Turn-on delay time	$t_{d(on)}$	V_{DS}=800V, I_D=40A, Gate Driver =-18V to 0V, $R_{G,EXT}$ = 1Ω, Inductive Load, FWD: UJ3D1220KSD T_J = 25°C		25		ns
Rise time	t_r			37		
Turn-off delay time	$t_{d(off)}$			48		
Fall time	t_f			39		
Turn-on energy	E_{ON}			935		µJ
Turn-off energy	E_{OFF}			828		
Total switching energy	E_{TOTAL}			1763		
Turn-on delay time	$t_{d(on)}$	V_{DS}=800V, I_D=40A, Gate Driver =-18V to 0V, $R_{G,EXT}$ = 1Ω, Inductive Load, FWD: UJ3D1220KSD T_J = 150°C		24		ns
Rise time	t_r			35		
Turn-off delay time	$t_{d(off)}$			43		
Fall time	t_f			37		
Turn-on energy	E_{ON}			880		µJ
Turn-off energy	E_{OFF}			800		
Total switching energy	E_{TOTAL}			1680		

Thermal Characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction-to-case	$R_{\theta JC}$			0.27	0.35	°C/W

Typical Performance Diagrams

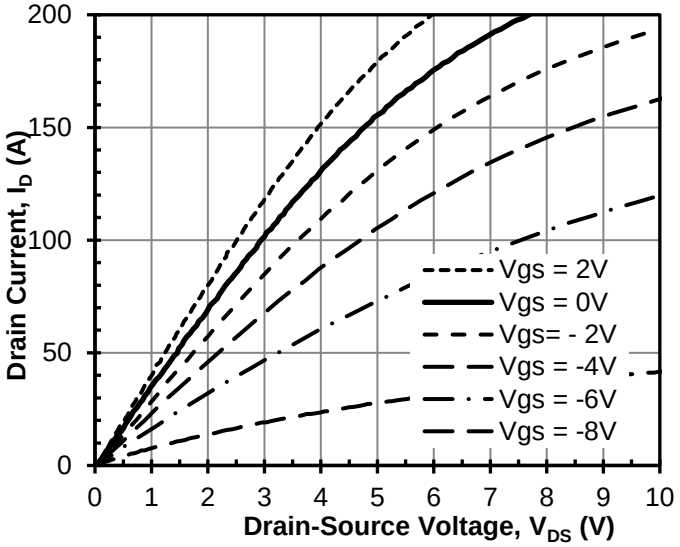


Figure 1 Typical output characteristics at T_J = -55°C

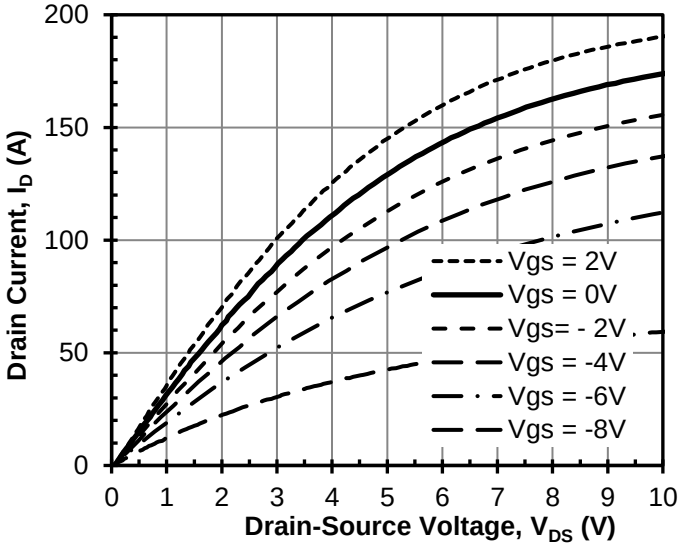


Figure 2 Typical output characteristics at T_J = 25°C

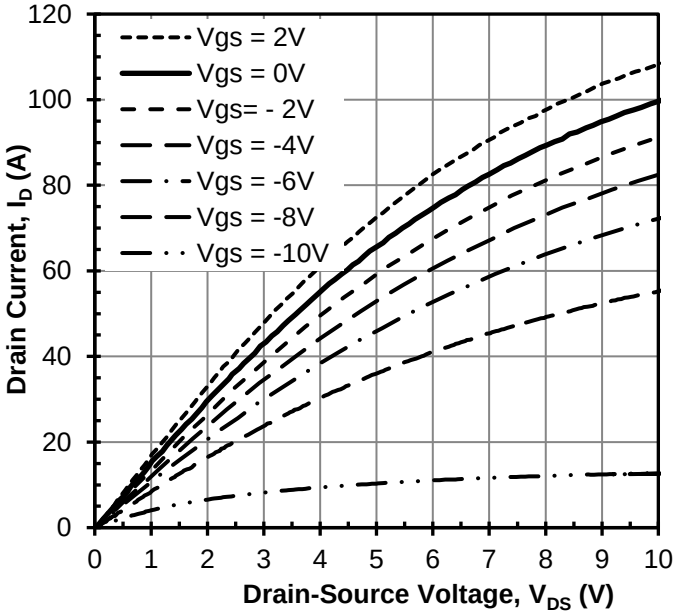


Figure 3 Typical output characteristics at T_J = 175°C

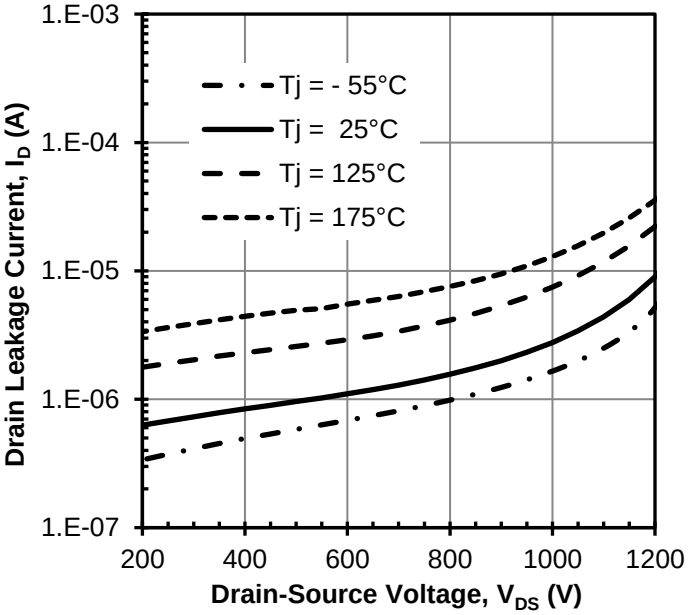


Figure 4 Typical drain-source leakage at V_{GS} = -20V

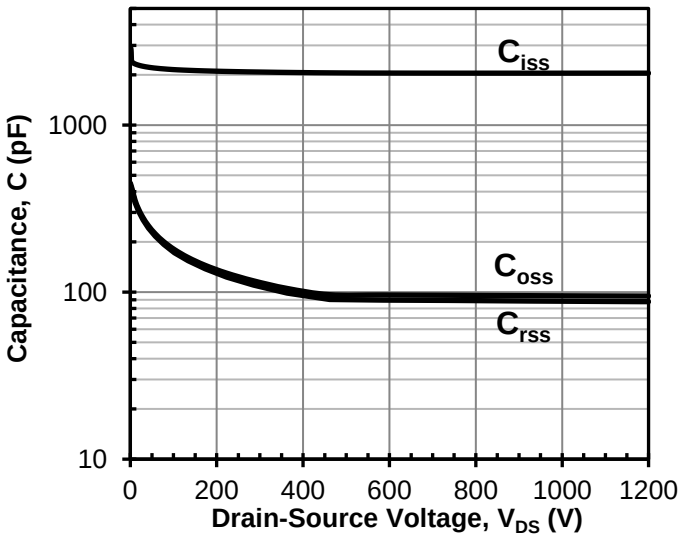


Figure 5 Typical capacitances at 100kHz and V_{GS} = -20V

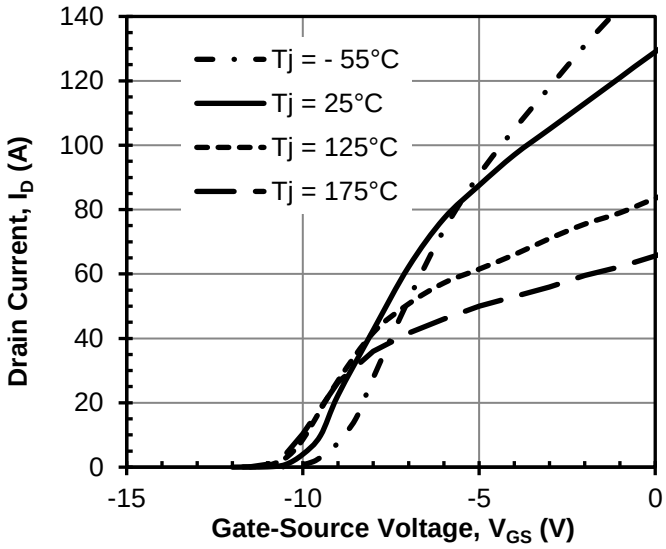


Figure 6 Typical transfer characteristics at V_{DS} = 5V

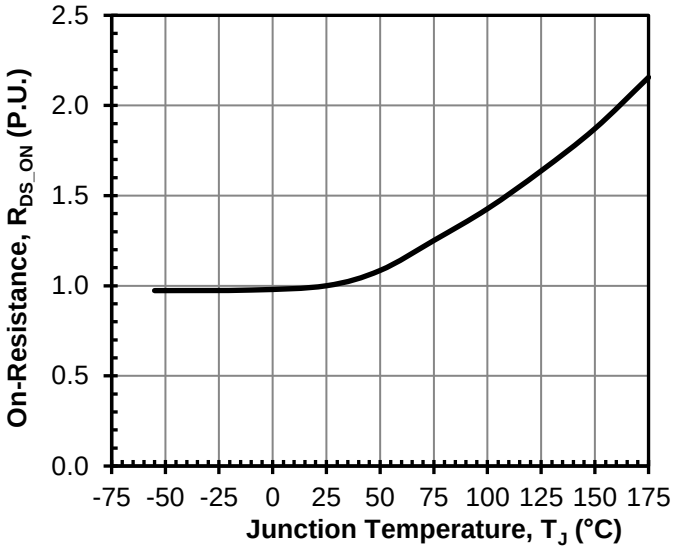


Figure 7 Normalized on-resistance vs. temperature at V_{GS} = 0V and I_D = 20A

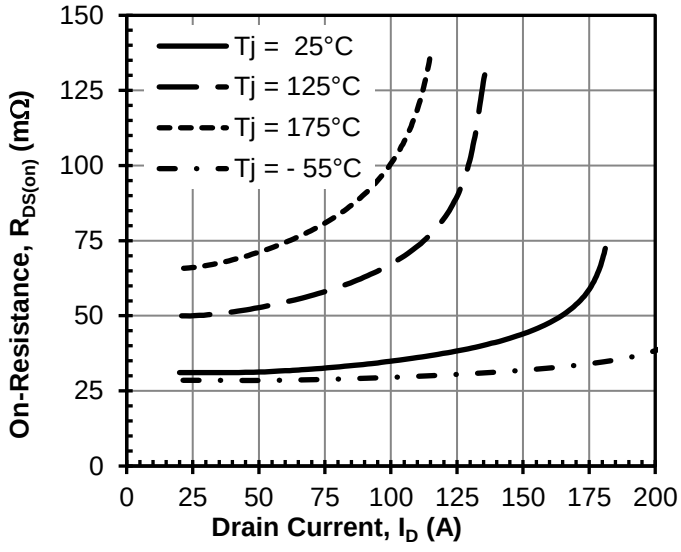


Figure 8 Typical drain-source on-resistance at V_{GS} = 0V

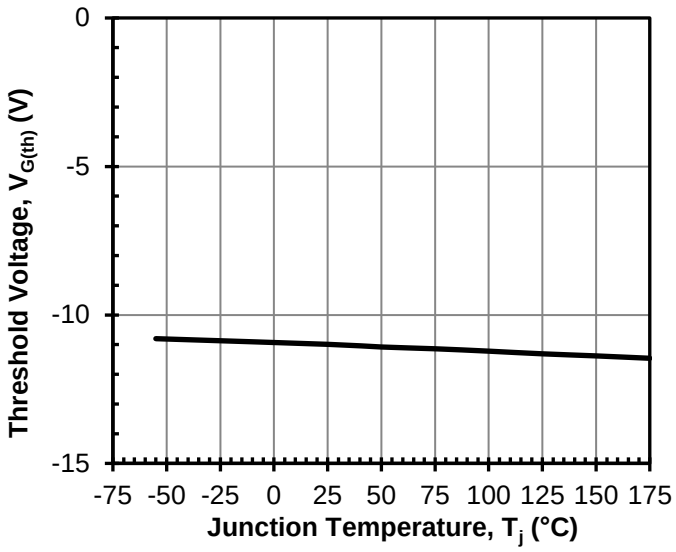


Figure 9 Threshold voltage vs. Tj at V_{DS} = 5V and I_D = 70mA

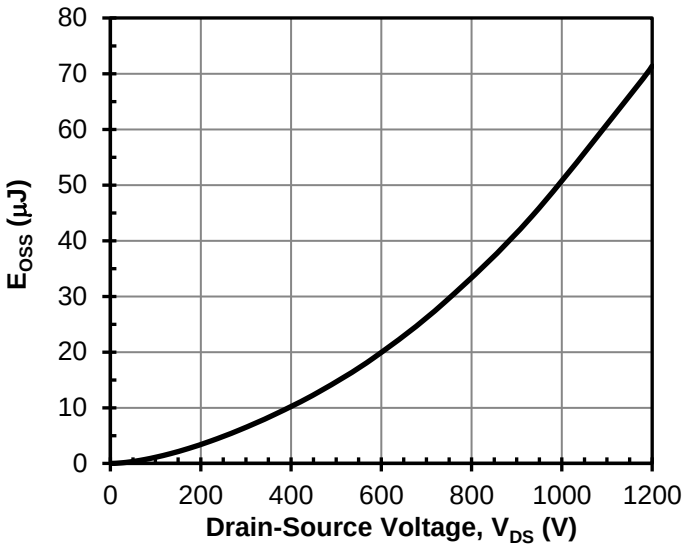


Figure 10 Typical stored energy in C_{OSS} at V_{GS} = -20V

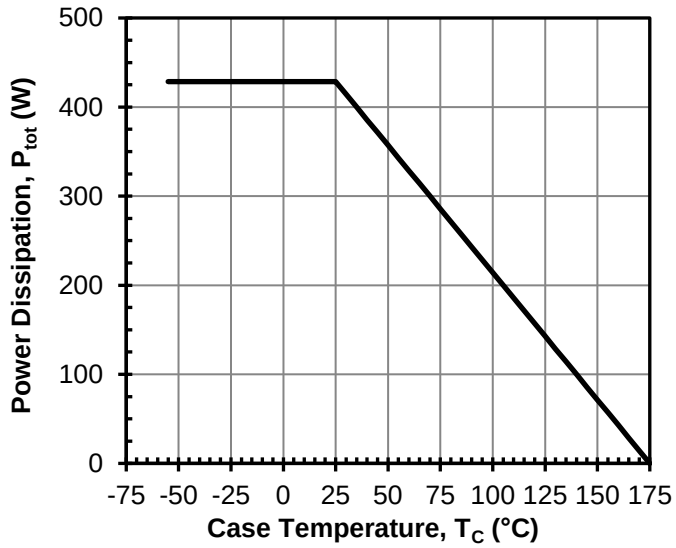


Figure 11 Total power Dissipation

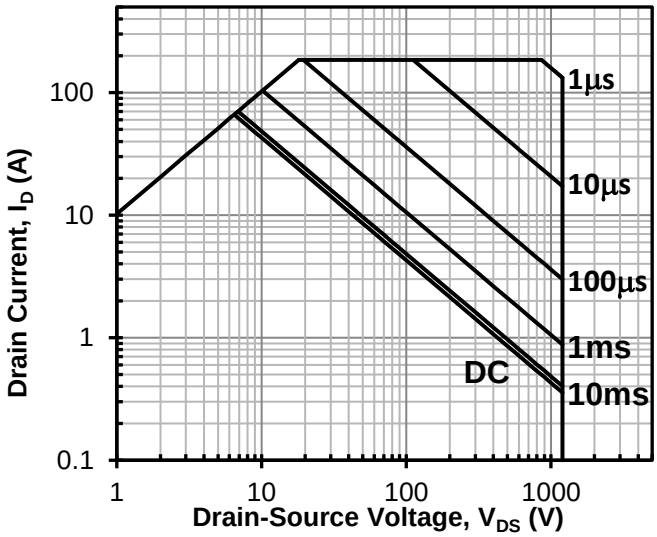


Figure 12 Safe operation area T_c = 25°C, Parameter t_p

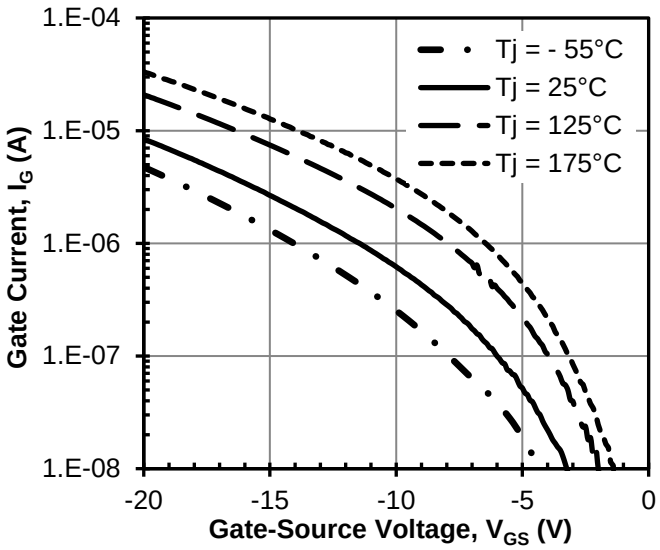


Figure 13 Typical gate leakage current at V_{DS} = 0V

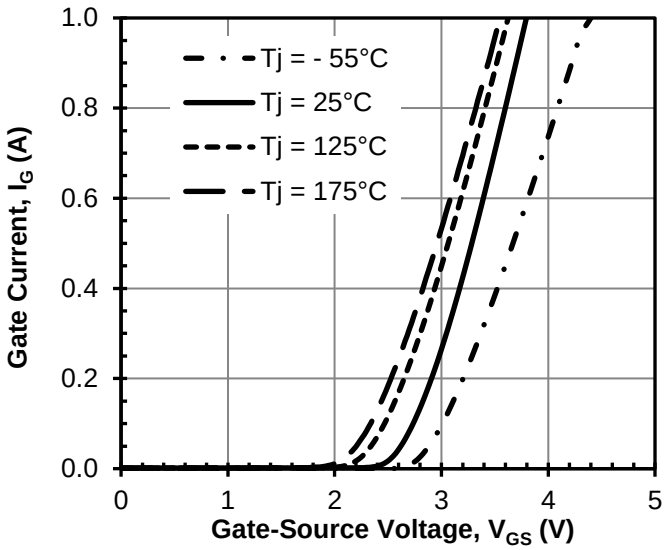


Figure 14 Typical gate forward current at V_{DS} = 0V

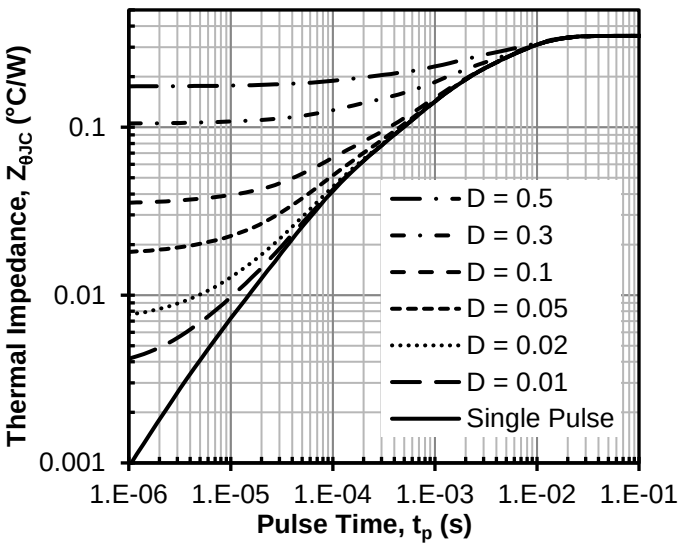


Figure 15 Maximum transient thermal impedance

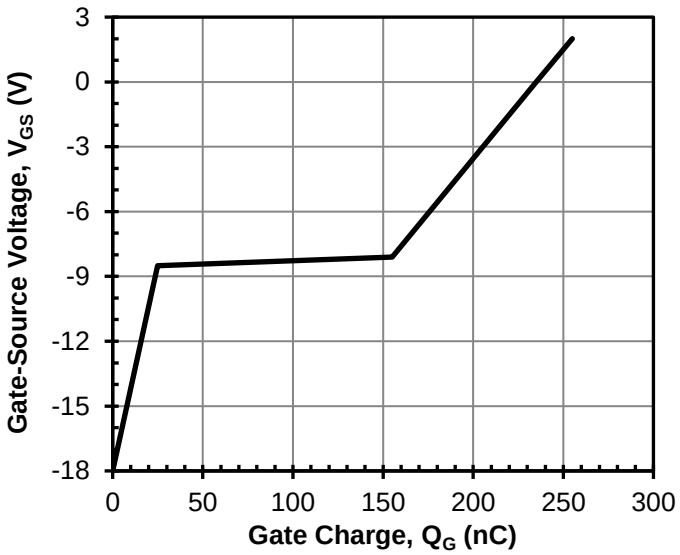


Figure 16 Typical gate charge at V_{DS} = 800V and I_D = 40A

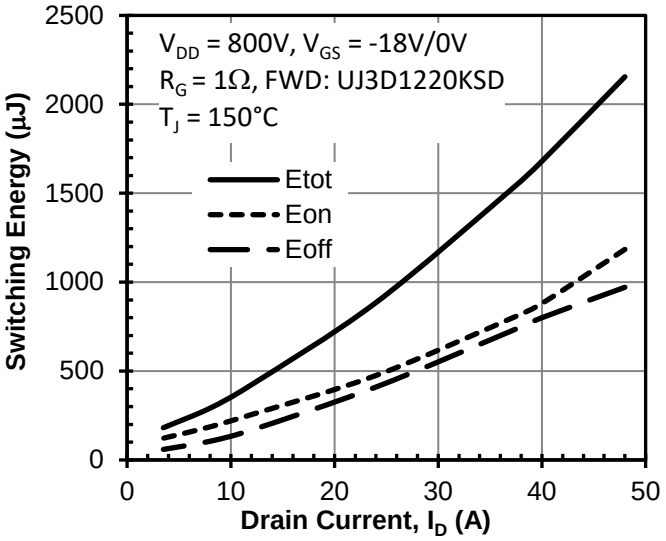


Figure 17 Clamped inductive switching energy vs. drain current at T_J = 150°C

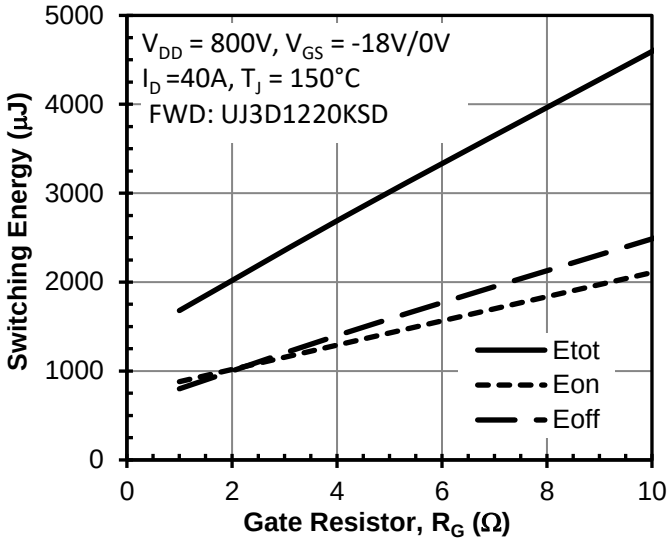


Figure 18 Clamped inductive switching energy vs. gate resistor R_G

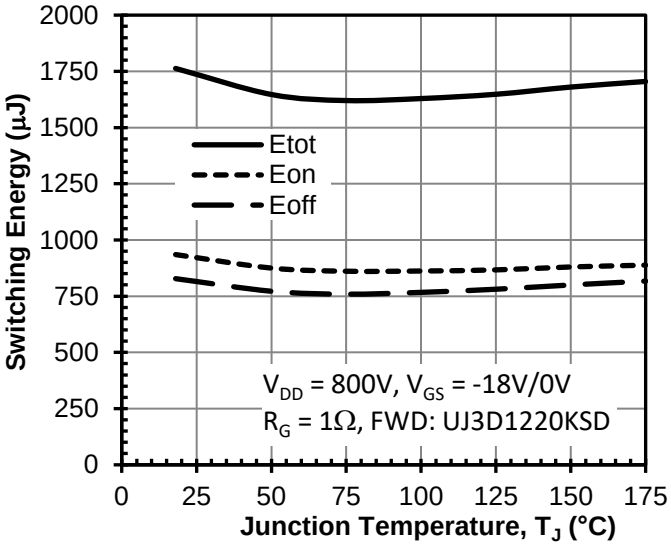


Figure 19 Clamped inductive switching energy vs. junction temperature at I_D = 40A

Disclaimer

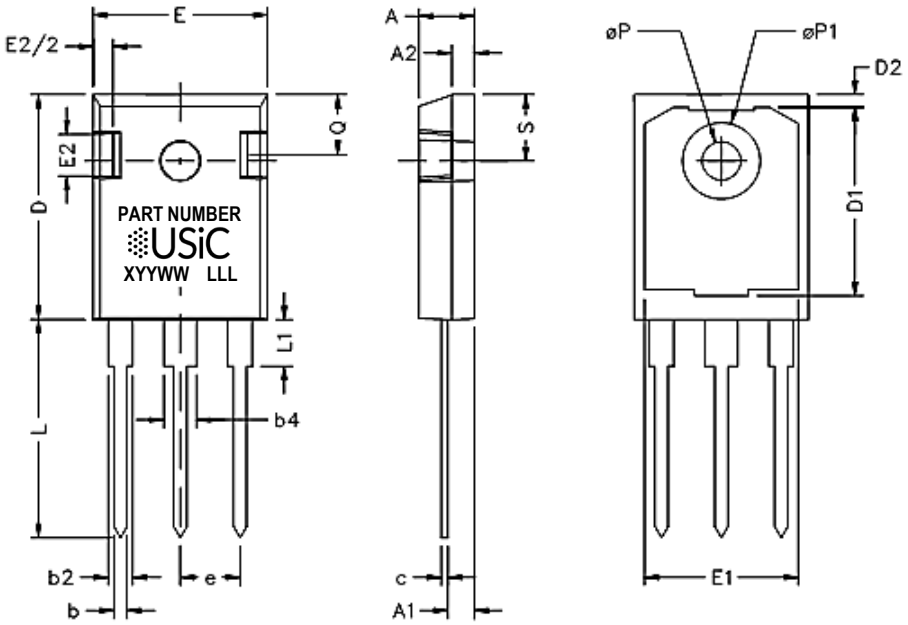
United Silicon Carbide, Inc. reserves the right to change or modify any of the products and their inherent physical and technical specifications without prior notice. United Silicon Carbide, Inc. assumes no responsibility or liability for any errors or inaccuracies within.

Information on all products and contained herein is intended for description only. No license, express or implied, to any intellectual property rights is granted within this document.

United Silicon Carbide, Inc. assumes no liability whatsoever relating to the choice, selection or use of the United Silicon Carbide, Inc. products and services described herein.

TO-247-3L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

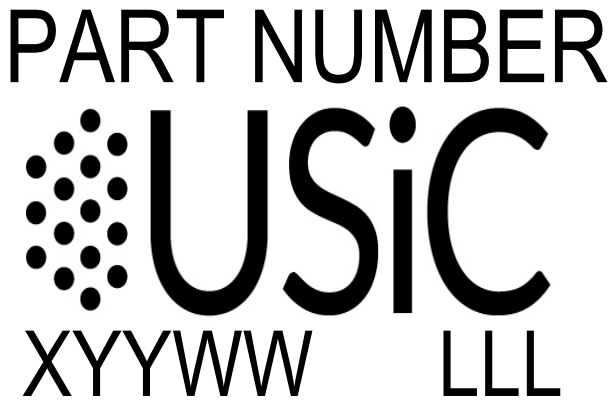
PACKAGE OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.185	0.209	4.699	5.309
A1	0.087	0.102	2.21	2.61
A2	0.059	0.098	1.499	2.489
b	0.039	0.055	0.991	1.397
b2	0.065	0.094	1.651	2.388
b4	0.102	0.135	2.591	3.429
c	0.015	0.035	0.381	0.889
D	0.819	0.845	20.803	21.463
D1	0.515	-	13.081	-
D2	0.02	0.053	0.508	1.346
E	0.61	0.64	15.494	16.256
e	0.214 BSC		5.44 BSC	
E1	0.53	-	13.462	-
E2	0.135	0.157	3.429	3.988
L	0.78	0.8	19.812	20.32
L1	-	0.177	-	4.496
ØP	0.14	0.144	3.556	3.658
ØP1	0.278	0.291	7.061	7.391
Q	0.212	0.244	5.385	6.198
S	0.243 BSC		6.17 BSC	

TO-247-3L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

PART MARKING



PART NUMBER = REFER TO DS_PN DECODER FOR DETAILS

X = ASSEMBLY SITE
YY = YEAR
WW = WORK WEEK
LLL = LOT ID

PACKING TYPE

ANTI-STATIC TUBE

QUANTITY /TUBE : 30 UNITS

DISCLAIMER

United Silicon Carbide, Inc. reserves the right to change or modify any of the products and their inherent physical and technical specifications without prior notice. United Silicon Carbide, Inc. assumes no responsibility or liability for any errors or inaccuracies within.

Information on all products and contained herein is intended for description only. No license, express or implied, to any intellectual property rights is granted within this document.

United Silicon Carbide, Inc. assumes no liability whatsoever relating to the choice, selection or use of the United Silicon Carbide, Inc. products and services described herein.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales